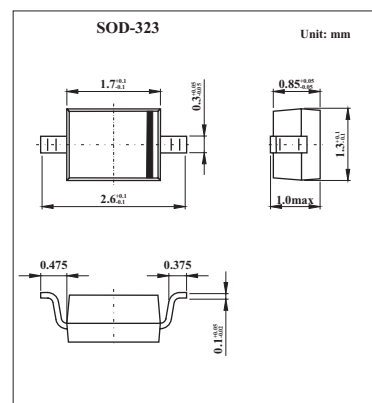


Schottky barrier diode

1PS76SB10

■ Features

- Low forward voltage
- Guard ring protected
- Very small plastic SMD package.

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

PARAMETER	SYMBOL	CONDITIONS	MIN	MAX	UNIT
continuous reverse voltage	V_R			30	V
continuous forward current	I_F			200	mA
repetitive peak forward current	T_{FRM}	$t_p \leq 1 \text{ s}; \delta \leq 0.5$		300	mA
non-repetitive peak forward current	T_{FSM}	$t_p < 10 \text{ ms}$		600	mA
storage temperature	T_{stg}		-65	+150	$^\circ\text{C}$
junction temperature	T_j			125	$^\circ\text{C}$
operating ambient temperature	T_{amb}		-65	+125	$^\circ\text{C}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

PARAMETER	SYMBOL	CONDITIONS	MAX	UNIT
forward voltage	V_F	$I_F = 0.1 \text{ mA}$	240	mV
		$I_F = 1 \text{ mA}$	320	
		$I_F = 10 \text{ mA}$	400	
		$I_F = 30 \text{ mA}$	500	
		$I_F = 100 \text{ mA}$	800	
reverse current	I_R	$V_R = 25 \text{ V}$; note 1;	2	μA
diode capacitance	C_d	$f = 1 \text{ MHz}; V_R = 1 \text{ V}$;	10	pF

Note

1. Pulsed test: $t_p = 300 \mu\text{s}$; $\delta = 0.02$.

■ Marking

Marking	S0
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